

IN THE CLAIMS

Please cancel Claims 21-27 and 34, without prejudice or disclaimer.

STATUS OF THE CLAIMS

Claims 1-20 (previously canceled).

Claims 21-27 (currently canceled).

Claim 28 (previously amended): A field effect transistor comprising:

a Si-containing semiconductor substrate;

spaced apart source/drain regions in said substrate defining a channel region therein;

a dielectric layer located atop said channel region, said dielectric layer including a bottom SiO₂ layer and a top metal silicate layer; and
a gate electrode located directly on an upper horizontal surface of said top metal silicate layer.

Claim 29 (original): The field effect transistor of Claim 28, wherein said metal silicate comprises at least a metal selected from the group consisting of La, Hf, Y, Sc, Sr, Ba, Ti, Ta, W, Cr, Ca, Mg, Be, Pr, Nd and mixtures and alloys thereof.

Claim 30 (original): The field effect transistor of Claim 29, wherein said metal is La, Hf or Y.

Claim 31 (original): The field effect transistor of Claim 28, wherein said silicate is La silicate.

Claim 32 (previously canceled).

Claim 33 (original): The field effect transistor of Claim 28, wherein said gate electrode comprises polysilicon, W, Al or Pt.

Claim 34 (currently canceled).